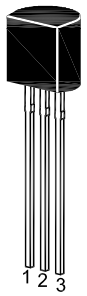
2SA1268

PNP Silicon Epitaxial Planar Transistor
For high voltage applications.

The transistor is subdivided into two groups, G and L according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	120	V
Collector Emitter Voltage	$-V_{CEO}$	120	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Emitter Current	I_E	100	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	- 55 to + 150	℃

Characteristics at T_a = 25℃

Parameter			Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 6 V, $-I_C$ = 2 mA	Current Gain Group	G	h_{FE}	200	-	400	-
		L	h_{FE}	350	-	700	-
Collector Base Cutoff Current at $-V_{CB}$ = 120 V			$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V			$-I_{EBO}$	-	-	100	nA
Collector Emitter Breakdown Voltage at $-I_C$ = 1 mA			$-V_{(BR)CEO}$	120	-	-	V
Collector Emitter Saturation Voltage at $-I_C$ = 10 mA, $-I_B$ = 1 mA			$-V_{CE(sat)}$	-	-	0.3	V
Gain Bandwidth Product at $-V_{CE}$ = 6 V, $-I_C$ = 1 mA			f_T	-	100	-	MHz
Output Capacitance at $-V_{CB}$ = 10 V, f = 1 MHz			C_{ob}	-	4	-	pF